

Performance

- Technology: 0.35um Power GaN HEMT
- Frequency: 2.3GHz
- Typical Pout : 39dBm(CW)
- Typical Gain: 14dB
- Typical PAE: 60%
- Bias: 28V/-4~-2V
- Package: Metal Ceramic



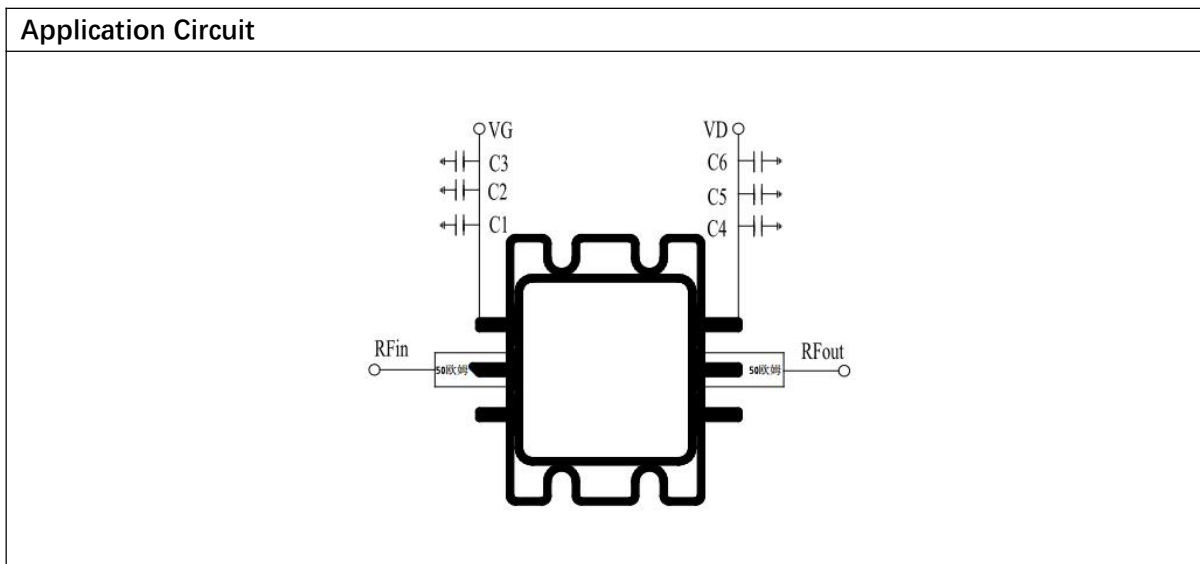
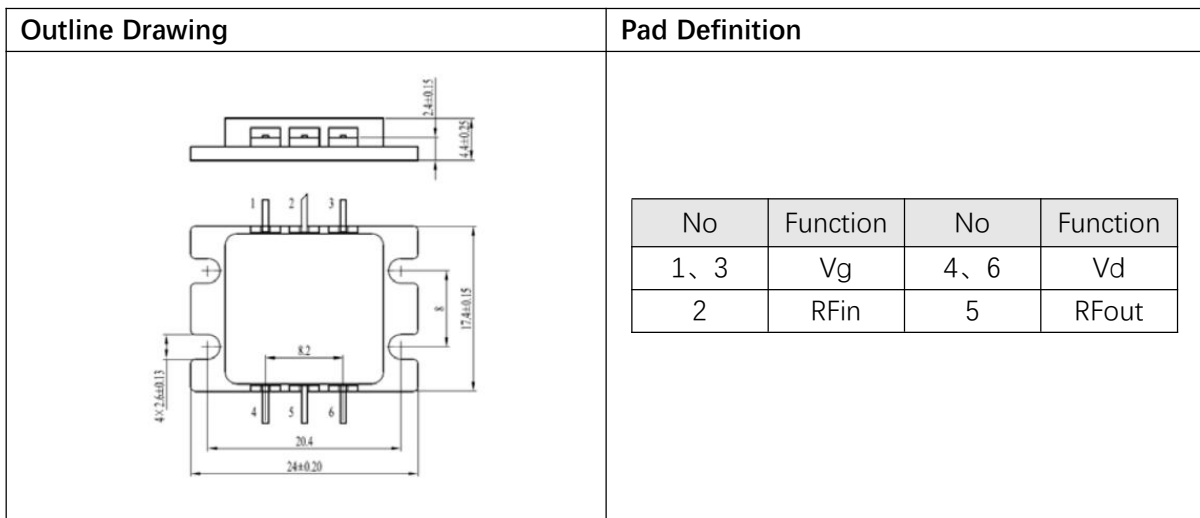
Electrical Specifications (TA=25°C, Vd=28V, CW, F: 2.3GHz)

Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	-	39	-	dBm
Gp	Power Gain	-	14	-	dB
η_{add}	Power Added Efficiency		60	-	%
ΔGp	Gain Flatness	-0.5	-	+0.5	dB
Rth	Thermal Resistance	-	-	15	°C/W

Absolute Max Ratings (TA=25°C)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	60V	
Vg	Grid Voltage	-5V	
Tch	Channel Temperature	225°C	【1】
Tm	Mounting Temperature	300°C	1 min, N2 Protection
Tstg	Storage Temperature	-55~175°C	
Tc	Operating Temperature	-55~85°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.



Note:

- (1) The typical packaging form is defined as C164-2 shell packaging;
- (2) Connect the circuit according to the diagram, pay attention to anti-static, and ensure good grounding and heat dissipation when using power devices;
- (3) In order to ensure the good performance of the power module, the capacity value of the power filter and the energy storage capacitor shall be reasonably selected according to the modulation mode during pulse operation;
- (4) C1=C4=100pf, C2=C5=1000pf, C3=47uf, C6=100uf.